

Product Manual

EKWIN ELECTRONICS CO.,LTD

EK TYN16105/18105

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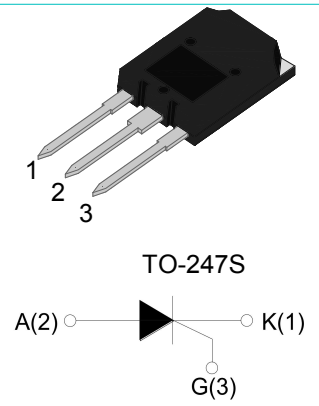


105A SCRs

TYNxx105 Serial

Main Features:

$I_{T(RMS)}$	V_{DRM}/V_{RRM}	I_{GT}
105A	1600V and 1800 V	10 - 80 mA



Description:

TYN16105/18105 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

Absolute Ratings(limiting values) :

Symbol	Parameter	Value	Unit
T_{stg}	Storage junction temperature range	- 40 to + 150	°C
T_j	Operating junction temperature range	- 40 to + 125	°C
$I_{T(AV)}$	Average on-state current	TO-247S (TC=80°C)	A
$I_{T(RMS)}$	RMS on-state current	TO-247S (TC=80°C)	A
I_{TSM}	Non repetitive surge peak on-state current (tp=10ms)	1250	A
V_{DRM}	Repetitive peak off-state voltage(Tj =25°C)	1600 and 1800	V
V_{RRM}	Repetitive peak reverse voltage(Tj =25°C)	1600 and 1800	V
I^2t	I^2t value for fusing tp = 10 ms	8000	A ² s
dI/dt	Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	150	A/μs
I_{GM}	Peak gate current	6	A

P_{G(AV)}	Average gate power dissipation	2	W
P_{GM}	Peak gate power	20	W

Electrical Characteristics : (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN	TYP	MAX	
I_{GT}	V _D =12V R _L =33Ω	10	-	80	mA
V_{GT}		--	-	1.5	V
V_{GD}	V _D =V _{DRM} T _j =125°C	0.25	--	--	V
I_L	I _G =1.2 I _{GT}	--	--	200	mA
I_H	I _T = 1A	--	--	150	mA
dv/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	1000	--	--	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I _{TM} = 80A tp= 380μs	T _j =25°C	1.8	V
I_{DRM} I_{RRM}	V _D =V _{DRM} , V _R =V _R RM	T _j =25°C	50	μ A
		T _j =125°C	10	mA

Thermal Resistances :

Symbol	Parameter		Value	Unit
R_{th(j-c)}	junction to case(DC)	TO-247S	0.27	°C/W

Fig.1: Maximum power dissipation versus RMS on-state current

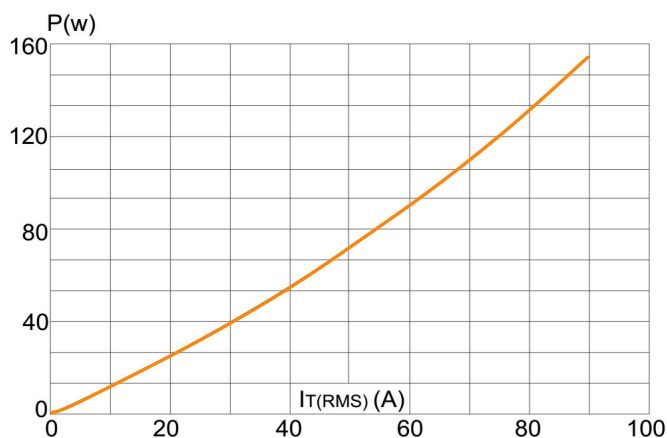


Fig.2 : RMS on-state current versus case temperature

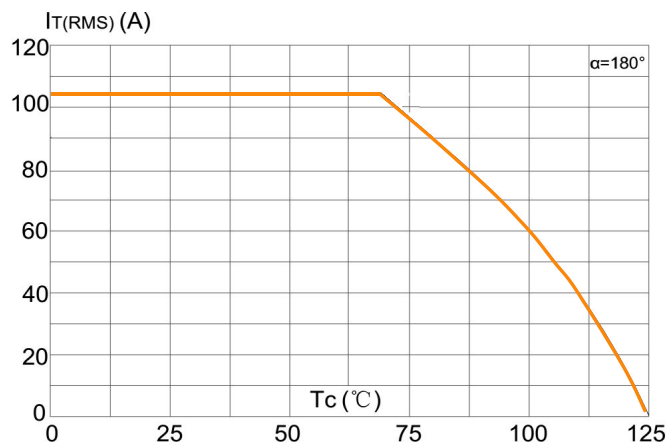


Fig.3 : Surge peak on-state current versus number of cycles

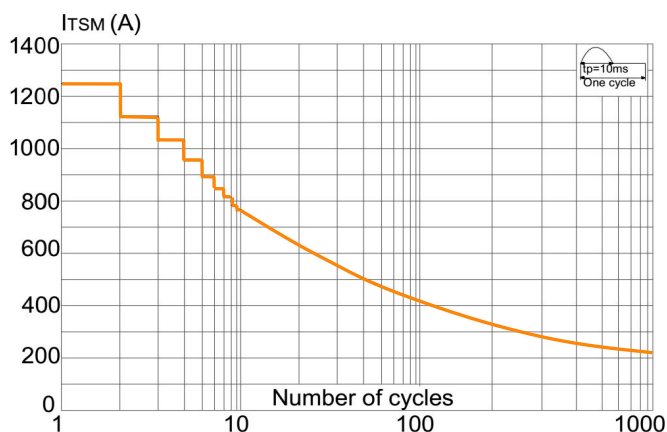


Fig.4 : On-state characteristics (maximum values)

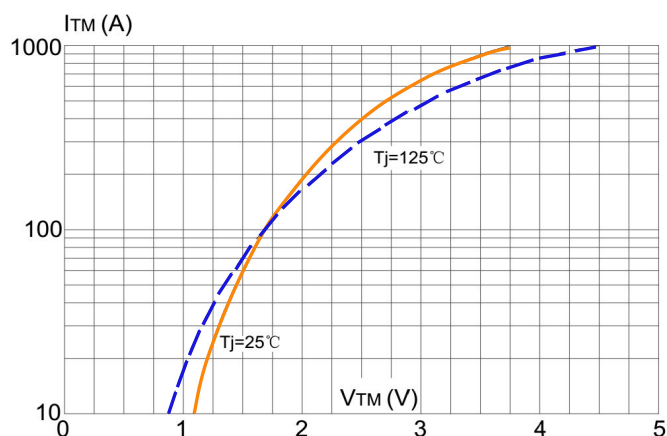


Fig.5 : Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$ and corresponding value of $I^2 t$

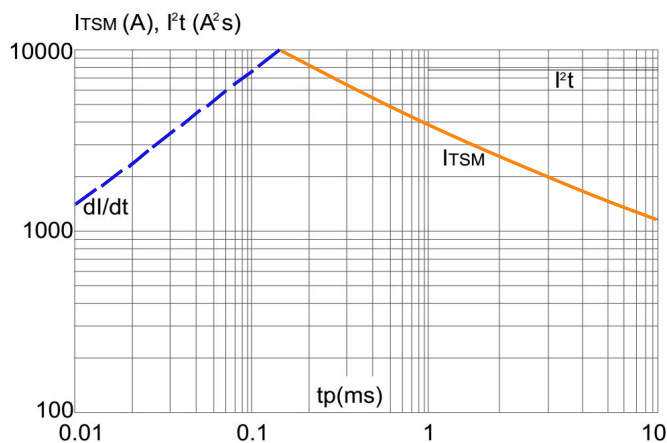
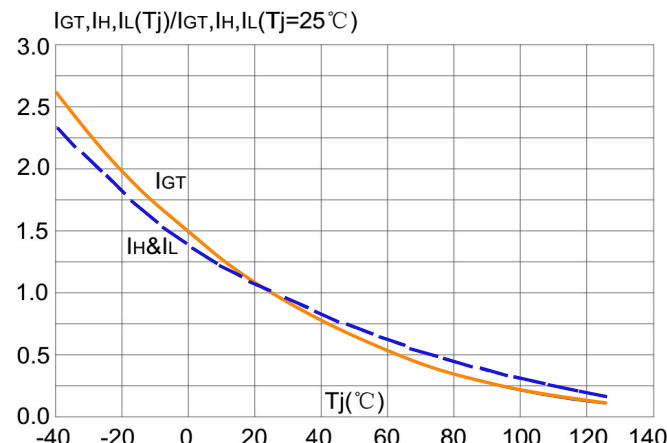
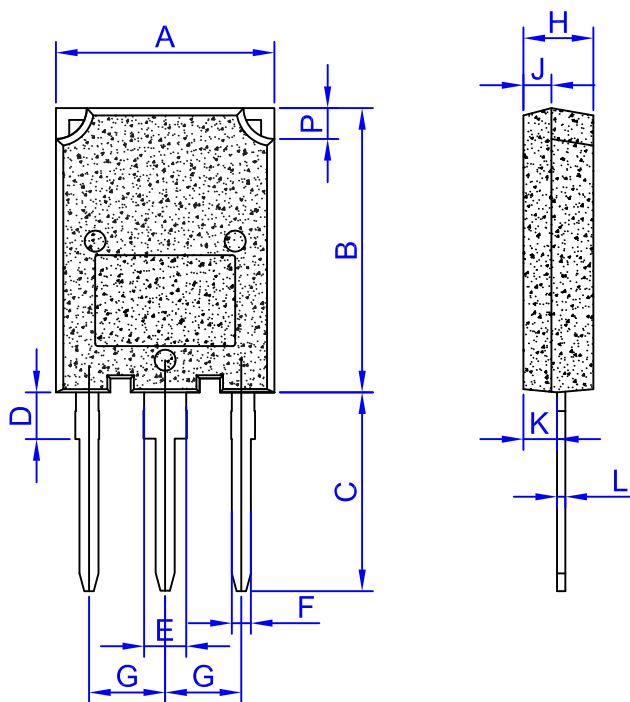


Fig.6: Relative variations of gate trigger current versus junction temperature



Package Mechanical Data :

TO-247S(TO-274AA)



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	15.1	16.1	0.595	0.632
B	19.8	20.8	0.78	0.818
C	13.8	14.8	0.544	0.582
D	3.0	4.0	0.118	0.157
E	2.75	3.35	0.108	0.132
F	1.3	1.5	0.051	0.059
G	5.1	5.8	0.201	0.228
H	4.5	5.5	0.178	0.216
J	1.45	2.15	0.058	0.084
K	1.9	2.8	0.075	0.110
L	0.55	0.8	0.022	0.032
P	2	2.4	0.079	0.095